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### Vishay Semiconductors

# Hyperfast Rectifier, 2 x 4 A FRED Pt®



#### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	2 x 4 A					
V <sub>R</sub>	200 V					
V <sub>F</sub> at I <sub>F</sub>	0.7 V					
t <sub>rr (typ.)</sub>	25 ns					
T <sub>J</sub> max.	175 °C					
Package	FlatPAK 5 x 6					
Circuit configuration	Separated cathode					

#### **FEATURES**

 Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

### **MECHANICAL DATA**

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		$V_{RRM}$		200	V		
Average rectified forward current	per device	I <sub>F(AV)</sub>	T <sub>Solderpad</sub> = 170 °C, DC	- 8	А		
Average rectilled forward current per device	per device		T <sub>Solderpad</sub> = 169 °C, D = 0.5	0			
Non-repetitive peak surge current	per device	1	$T_J = 25$ °C, 10 ms sinusoidal pulse	173			
per di	per diode	IFSM		87			
Operating junction and storage ten	nperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX.							
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage, per diode	W	I <sub>F</sub> = 4 A	-	0.87	0.96	6 V	
Forward voltage, per diode	V <sub>F</sub>	I <sub>F</sub> = 4 A, T <sub>J</sub> = 150 °C	-	0.7	0.78	7	
Reverse leakage current, per diode		V <sub>R</sub> = V <sub>R</sub> rated	-	-	2		
neverse leakage current, per diode	I <sub>R</sub>	$T_J = 150  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	7 80 µA			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	19	-	pF	



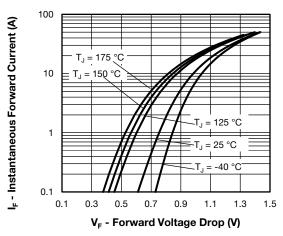
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A, } dI_F/dt =$	= 50 A/ $\mu$ s, $V_R$ = 30 V	ı	20	ı	
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		ı	ı	25	25 ns
heverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	17	-	115
		T <sub>J</sub> = 125 °C		-	29	-	
Dook receivery current	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4 A dI <sub>F</sub> /dt = 200 A/µs	-	2.1	-	۸
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 160 V	-	4	- A	
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		- 18 - nC			
neverse recovery charge	$Q_{rr}$	T <sub>J</sub> = 125 °C		-	60	-	nC

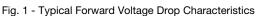
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Thermal resistance, junction to ambient, per diode	R <sub>thJA</sub> (1)(2)		-	89	103	°C/W	
Thermal resistance, junction to mount, per diode	R <sub>thJM</sub> (3)		-	1.8	2.1	G/ VV	

#### Notes

- $^{(1)}$  The heat generated must be less than the thermal conductivity from junction to ambient:  $dP_D/dT_J < 1/R_{thJA}$
- $^{(2)}$  Free air, mounted or recommended copper pad area; thermal resistance  $R_{thJA}$  junction to ambient
- (3) Mounted on infinite heatsink







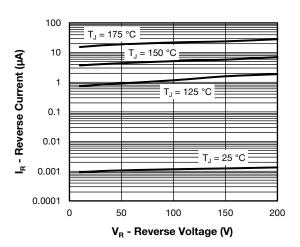


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

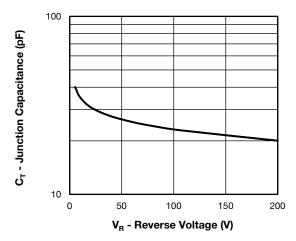


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

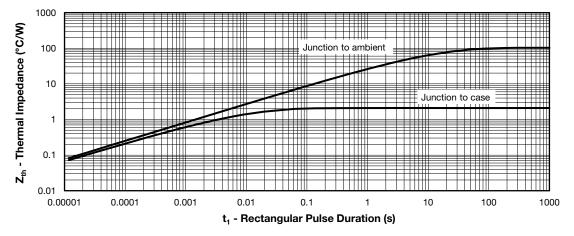


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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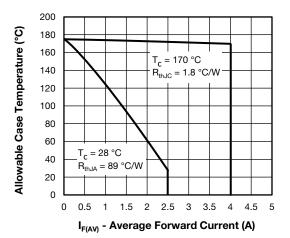


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

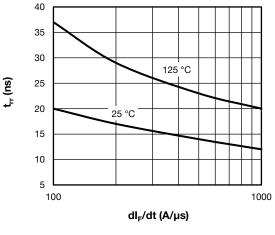


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

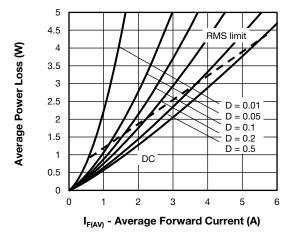


Fig. 6 - Forward Power Loss Characteristics

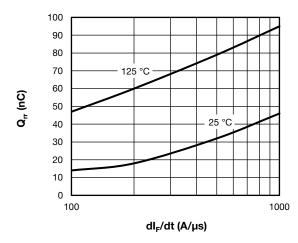
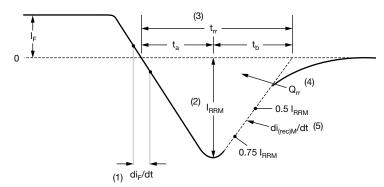


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $I_{r}$  to point where a line passing through 0.75  $I_{RRM}$  and 0.50  $I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

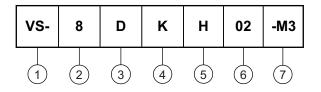
(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 9 - Reverse Recovery Waveform and Definitions



### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

Circuit configuration:

D = separated cathode

K = FlatPAK package

5 - Process type,

H = hyper fast recovery

6 - Voltage code (02 = 200 V)

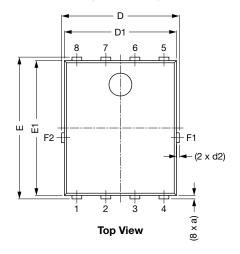
8 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

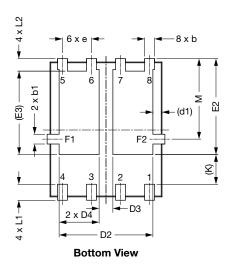
ORDERING INFORMATION (example)								
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-8DKH02-M3/H	0.10	Н	1500	7"diameter plastic tape and reel				
VS-8DKH02-M3/I	0.10	I	6000	13"diameter plastic tape and reel				

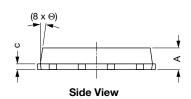
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96056				
Part marking information	www.vishay.com/doc?96059				
Packaging information	www.vishay.com/doc?88869				

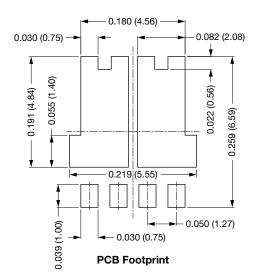
# FlatPAK 5 x 6 (Dual)

### **DIMENSIONS** in inches (millimeters)









DIM		INCHES			MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	0.035	0.039	0.043	0.89	0.99	1.09		
(a)	-	0.006	-	-	0.15	=		
b	0.013	0.017	0.020	0.32	0.43	0.52		
b1	0.013	0.017	0.020	0.32	0.43	0.52		
С	0.008	-	0.014	0.20	-	0.35		
D	0.197	0.203	0.209	5.00	5.15	5.30		
D1	0.189	0.193	0.197	4.80	4.90	5.00		
D2	0.154	0.161	0.169	3.90	4.10	4.30		
D3	0.020	0.024	0.031	0.50	0.60	0.80		
D4	0.063	0.069	0.075	1.60	1.75	1.90		
(d1)	-	0.016	-	-	0.40	=		
(d2)	-	0.005	-	-	0.125	-		
Е	0.238	0.244	0.250	6.05	6.20	6.35		



## **Outline Dimensions**

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DIM		INCHES	INCHES		MILLIMETERS		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
E1	0.228	0.232	0.236	5.80	5.90	6.00	
E2	0.157	0.165	0.173	4.00	4.20	4.40	
(E3)	-	0.144	=	-	3.65	-	
е		0.050 BSC			1.27 BSC		
(K)	0.039	-	=	1.00	-	=	
L1	0.019	-	0.043	0.48	-	1.10	
L2	0.012	-	0.031	0.30	-	0.80	
M	0.128	0.138	0.148	3.25	3.50	3.75	
Θ	0°	-	10°	0°	-	10°	

#### Notes

• Dimensioning and tolerancing per ASME Y14.5-2009

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- Dimensions D1 and E1 do not include mold flash or gate burrs
- Dimension (XX) means reference only



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